

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S22 6	21005	implant\$6 and (si silicon) near15 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:44
S22 7	11908	implant\$6 same (mask\$5 or pattern\$5) and (si silicon) near15 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:52
S23 1	2589	implant\$6 near15 (mask\$5 or pattern\$5) and (silicon or si) near5 substrate and (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:53
S23 0	3651	implant\$6 same (mask\$5 or pattern\$5) and (silicon or si) near5 substrate and (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:53
S22 9	10441	implant\$6 same (mask\$5 or pattern\$5) and (silicon or si) near5 substrate and (si silicon) near15 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:53
S22 8	10807	implant\$6 same (mask\$5 or pattern\$5) and (silicon or si) near10 substrate and (si silicon) near15 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:53
S23 2	1505	implant\$6 near15 (mask\$5 or pattern\$5) and (silicon or si) near5 substrate and (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5) and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:54
S23 3	577	implant\$6 near15 (mask\$5 or pattern\$5) and (silicon or si) near5 substrate same (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5) and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:55
S23 5	3	(germanium or ge or fluorine or f neutral) near10 implant\$6 near15 (mask\$5 or pattern\$5) and (silicon or si) near5 substrate same (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5) same anneal\$6 and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:58

S23 4	121	implant\$6 near15 (mask\$5 or pattern\$5) and (silicon or si) near5 substrate same (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5) same anneal\$6 and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:45
S22 3	29	(yvon near2 gris or germaine near2 troillard or jocelyne near2 mourier).in. and implant\$5 and (silicon or si) near10 single near2 crystal\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:45
S21	6	ion near4 implant\$4 same (fl or flourine or fluorine) same (silicon or si) and "117"/\$4.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:45
L3	30	(yvon near2 gris or germaine near2 troillard or jocelyne near2 mourier).in. and implant\$5 and (silicon or si) near10 single near2 crystal\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:45
L1	7	ion near4 implant\$4 same (fl or flourine or fluorine) same (silicon or si) and "117"/\$4.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:45
S22 1	80	(yvon near2 gris or germaine near2 troillard or jocelyne near2 mourier).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:46
S20 9	39	ion near3 (germanium or ge fluorine f) near3 implant\$5 near15 (si or silicon) near5 (substrate or wafer) near15 (mask\$4 or pattern\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:46
S18 6	101	(silicon or si) near5 (substrate or wafer) same implant\$5 near10 (neutral\$4 or fluorine or carbon or germanium or tin or sb or ge) same (photo\$1resist or resist or mask\$4) same (si or silicon) near4 deposit\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:46
L7	121	implant\$6 near15 (mask\$5 or pattern\$5) and (silicon or si) near5 substrate same (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5) same anneal\$6 and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:46

L6	102	(silicon or si) near5 (substrate or wafer) same implant\$5 near10 (neutral\$4 or fluorine or carbon or germanium or tin or sb or ge) same (photo\$1resist or resist or mask\$4) same (si or silicon) near4 deposit\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:46
L5	40	ion near3 (germanium or ge fluorine f) near3 implant\$5 near15 (si or silicon) near5 (substrate or wafer) near15 (mask\$4 or pattern\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:46
L4	82	(yvon near2 gris or germaine near2 troillard or jocelyne near2 mourier).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:46
L2	121	implant\$6 near15 (mask\$5 or pattern\$5) and (silicon or si) near5 substrate same (si silicon) near15 temperature near10 (deposit\$5 or epitax\$5) same anneal\$6 and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:46
L8	82	(yvon near2 gris or germaine near2 troillard or jocelyne near2 mourier).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:52
L12	11	implant\$5 near10 (carbon or germanium or fluoride) same epitax\$6 near5 (si or silicon) near15 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:53
L11	112	implant\$5 near10 (carbon or germanium or fluoride) and epitax\$6 near5 (si or silicon) near15 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:53
L10	334	implant\$5 near10 (si or carbon or germanium or fluoride) and epitax\$6 near5 (si or silicon) near15 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:53
L9	1150	implant\$5 and epitax\$6 near5 (si or silicon) near15 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/09 18:53